

Substitute for Form 1449 A & B/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application Number	10/050,570
(use as many sheets as necessary)		Confirmation Number	7078
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		First Named Inventor	Kuniaki YAGI
		Art Unit	1765
		Examiner Name	SONG, MATTHEW
		Attorney Docket Number	Q68148
Sheet <b>b1</b>	1	of	1

## **U.S. PATENT DOCUMENTS**

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## **FOREIGN PATENT DOCUMENTS**

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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
M)	'	BJÖRKETUN, L.-O. et al., "Interfacial Void Formation During Vapor Phase Growth of 3C-SiC on Si(0 0 1) and Si (1 1 1) Substrates Characterization by Transmission Electron Microscopy," Journal of Crystal Growth, December 1997, pp. 379-388, Vol. 182, No. 3-4, North-Holland Publishing Co., Amsterdam, NL.	
M S	'	YAGI, K. et al., "3C-SiC Growth By Alternate Supply of SiH <sub>2</sub> Cl <sub>2</sub> and C <sub>2</sub> H <sub>2</sub> ," Journal of Crystal Growth, April 1997, pp. 653-657, Vol. 174, No. 1-4, North-Holland Publishing Co., Amsterdam, NL.	
M)	'	STECKL, A.J. et al., "Epitaxial Growth of $\beta$ -SiC on Si by RTCVD with C <sub>3</sub> H <sub>8</sub> and SiH <sub>4</sub> ," IEEE Transactions on Electron Devices, January 1992, pp. 64-74, Vol. 39, No. 1, IEEE Inc., New York, US.	

**Examiner Signature**

#### Date Considered

3/1/2004

905/2003

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